

1                   ABSTRACT OF THE DISCLOSURE

2                   A semiconductor processing method of forming a plurality of  
3                   conductive lines includes, a) providing a substrate; b) providing a first  
4                   conductive material layer over the substrate; c) providing a first  
5                   insulating material layer over the first conductive layer; d) etching  
6                   through the first insulating layer and the first conductive layer to the  
7                   substrate to both form a plurality of first conductive lines from the first  
8                   conductive layer and provide a plurality of grooves between the first  
9                   lines, the first lines being capped by first insulating layer material, the  
10                   first lines having respective sidewalls; e) electrically insulating the first  
11                   line sidewalls; and f) after insulating the sidewalls, providing the  
12                   grooves with a second conductive material to form a plurality of second  
13                   lines within the grooves which alternate with the first lines. Integrated  
14                   circuitry formed according to the method, and other methods, is also  
15                   disclosed.

16

17

18

19

20

21

22

23

24